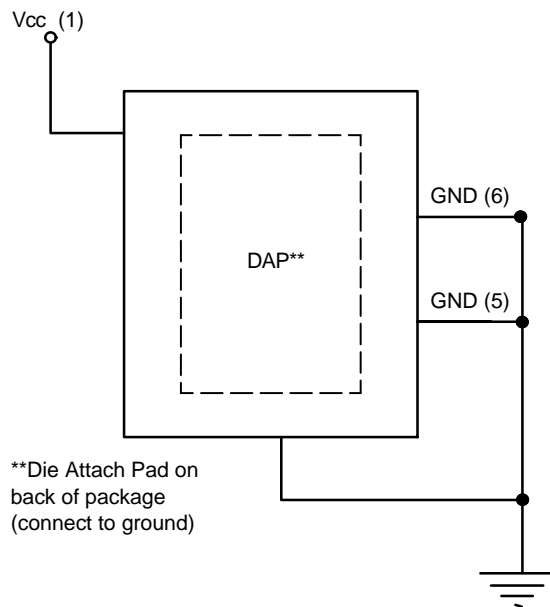# NSPM8151, NSPM8181

15 V and 18 V Unidirectional ESD and Surge Protection Device

Features

- Unidirectional High Voltage ESD & Surge Protection Device
- Provides ESD Protection to IEC61000−4−2 Level 4: ±30 kV Contact Discharge
- IEC 61000−4−5 (lighting)
- High Voltage Zener Diode Protects Supply Rail up to 100 A (8/20 μs)
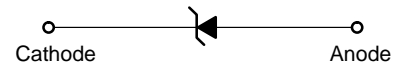- These Devices are Pb−Free and are RoHS Compliant

ON Semiconductor®

UDFN6
D4 SUFFIX
CASE 517CS

APPLICATION DIAGRAM

Vcc (1)

DAP**

GND (6)

GND (5)

**Die Attach Pad on back of package (connect to ground)

BLOCK DIAGRAM

Cathode   Anode

MARKING DIAGRAM

Ax M

1

Ax = Specific Device Code
x = 5 or E
M = Date Code
■ = Pb−Free Package

ORDERING INFORMATION

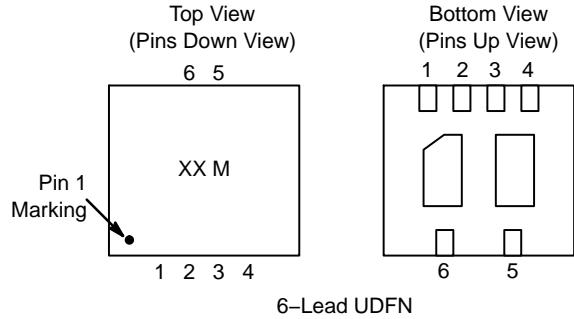| Device	Package	Shipping†
NSPM8151MUTBG	UDFN6 (Pb−Free)	3000 / Tape & Reel
NSPM8181MUTBG	UDFN6 (Pb−Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

Table 1. PIN DESCRIPTIONS

4–Channel, 6–Lead, UDFN–8 Package			
Pin	Name	Type	Description
1	V_{CC}	HV V_{DD}	HV ESD Channel
2	N/C		No Connect
3	N/C		No Connect
4	N/C		No Connect
5	GND		Ground
6	GND		Ground

PACKAGE / PINOUT DIAGRAMS

Top View
(Pins Down View)

6 5

XX M

Pin 1
Marking

1 2 3 4

Bottom View
(Pins Up View)

1 2 3 4

6   5

6–Lead UDFN

ELECTRICAL CHARACTERISTICS

Symbol	Parameter
I_{PP}	Maximum Reverse Peak Pulse Current
V_C	Clamping Voltage @ I_{PP}
V_{RWM}	Working Peak Reverse Voltage
I_R	Maximum Reverse Leakage Current @ V_{RWM}
V_{BR}	Breakdown Voltage @ I_T
I_T	Test Current
ΘV_{BR}	Maximum Temperature Coefficient of V_{BR}
I_F	Forward Current
V_F	Forward Voltage @ I_F

Uni−Directional Surge Protection
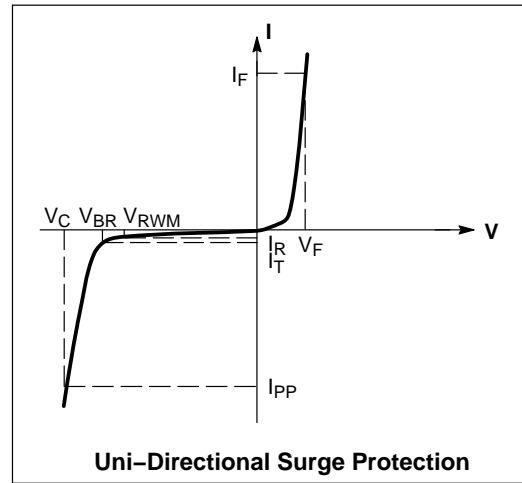
SPECIFICATIONS

Table 2. ABSOLUTE MAXIMUM RATINGS

Parameter		Rating	Units
Operating Temperature Range		−55 to +125	°C
Storage Temperature Range		−65 to +150	°C
Peak Current (t_p = 8/20 µs)	NSPM8151	100	A
Peak Current (t_p = 8/20 µs)	NSPM8181	119	A

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

ELECTRICAL CHARACTERISTICS

Device Name	Device Marking	V_{RWM} (V) (Note 1) Max	I_R @ V_{RWM} (µA) Max	Breakdown Voltage				V_C @ I_{PP} (8 x 20 µs) (Note 3)	
				V_{BR} V (Note 2)			@ I_T (mA)	V_C (V)	I_{PP} (A)
				Min	Nom	Max		Max	
NSPM8151	A5	15	1	16	17.5	18.5	1	27	100
NSPM8181	A8	18	1	20	22.5	23.5	1	28 30	70 100

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.
1. A surge protector is normally selected according to the working peak reverse voltage (V_{RWM}), which should be equal to or greater than the DC or continuous peak operating voltage level.
2. V_{BR} measured at pulse test current I_T at an ambient temperature of 25°C.
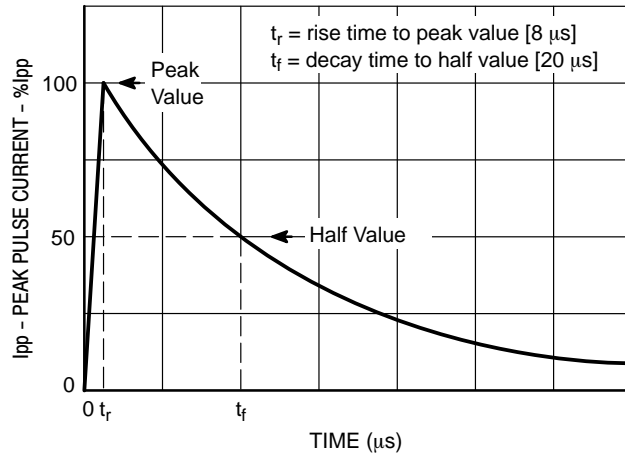3. Surge current waveform per Figure 1.

TYPICAL CHARACTERISTICS

Figure 1. IEC61000−4−5 8/20 μs Pulse Waveform

MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

ON Semiconductor®
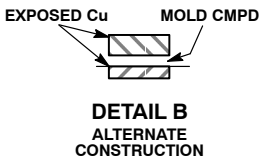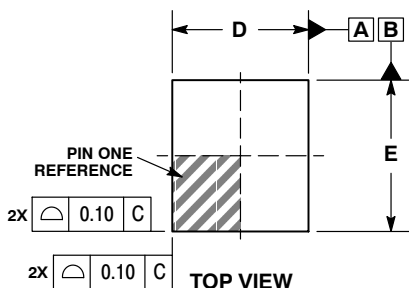
**UDFN6, 1.8x2, 0.4P**
CASE 517CS
ISSUE O

DATE 30 APR 2013

SCALE 4:1

TOP VIEW

PIN ONE REFERENCE

2X | 0.10 | C

2X | 0.10 | C

DETAIL B
ALTERNATE CONSTRUCTION

EXPOSED Cu   MOLD CMPD

DETAIL A
ALTERNATE CONSTRUCTIONS

SIDE VIEW

| 0.05 | C

6X

| 0.05 | C

NOTE 4

DETAIL B

A3

A

A1

SEATING PLANE C

BOTTOM VIEW

DETAIL A

2X D2

| 0.10 | C

2X E2

6X L

| 0.10 | C

e1/2

e1

SUPPLEMENTAL BOTTOM VIEW

e/2

e

6X b

| 0.07 | C | A | B
| 0.05 | C | NOTE 3

e2

NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b APPLIES TO PLATED TERMINALS AND IS MEASURED BETWEEN 0.15 AND 0.30mm FROM THE TERMINAL TIP.
4. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.

DIM	MILLIMETERS	
	MIN	MAX
A	0.45	0.55
A1	0.00	0.05
A3	0.125 REF	
b	0.15	0.25
D	1.80 BSC	
D2	0.35	0.55
E	2.00 BSC	
E2	0.74	0.94
e	0.40 BSC	
e1	0.80 BSC	
e2	0.95 BSC	
L	0.20	0.40
L1	---	0.15
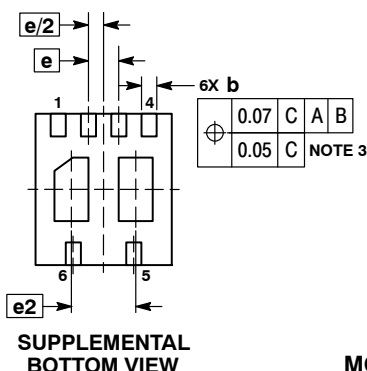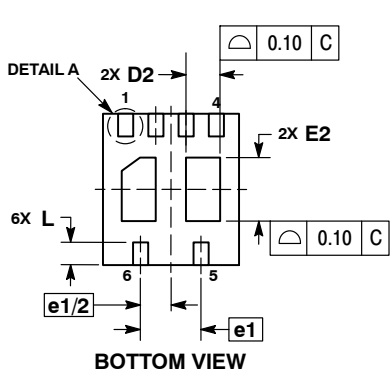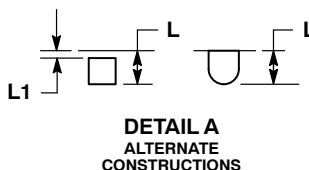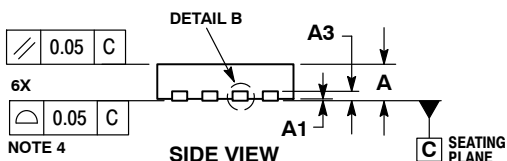
GENERIC MARKING DIAGRAM*

XX M
1

XX = Specific Device Code
M = Date Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb–Free indicator, "G" or microdot " ∎ ", may or may not be present.

RECOMMENDED MOUNTING FOOTPRINT*

0.40 PITCH

0.95

6X 0.48

2X 0.55

PACKAGE OUTLINE

2X 0.94

2.20

6X 0.25

0.40 PITCH

DIMENSIONS: MILLIMETERS
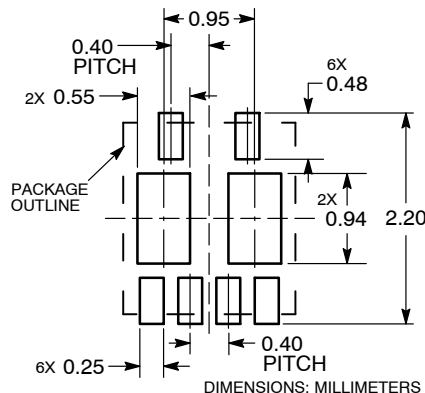
*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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DESCRIPTION:	UDFN6 1.8X2, 0.4P	PAGE 1 OF 1

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PUBLICATION ORDERING INFORMATION

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